

Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 130 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	8	A
Static chara	cteristics				·	·	
V _F	forward voltage	I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
Dynamic cha	aracteristics	·	1	1			
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	12	18	ns





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K A
2	А	anode	$2 \circ 4$	001aaa020
mb	mb	mounting base; connected to cathode	C	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYC8-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC8-600P	BYC8-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 130 °C; square-wave pulse; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 130 °C; square-wave pulse	-	16	A
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Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	91	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	100	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

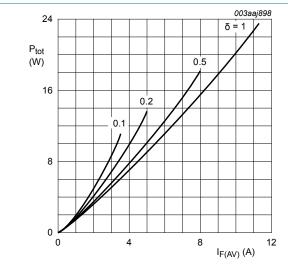
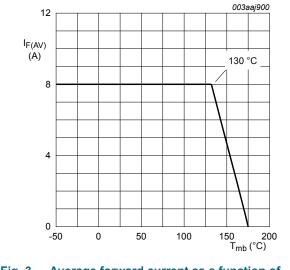


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$
$V_{O} = 1.581 \text{ V}; R_{S} = 0.043 \Omega$





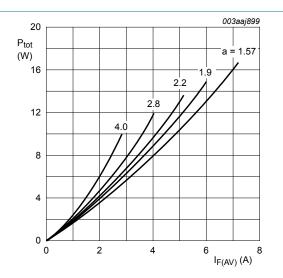
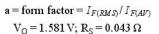
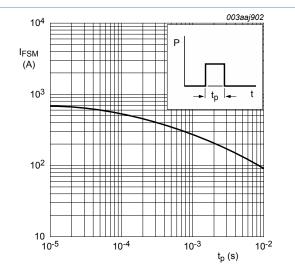


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



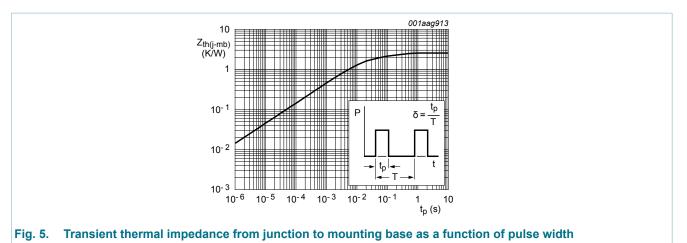




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9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



10. Characteristics

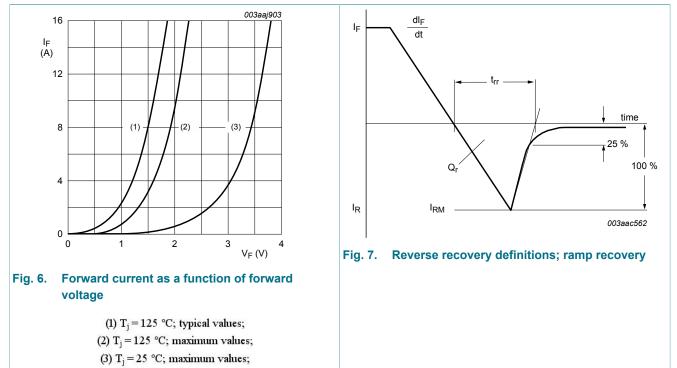
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.4	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	20	μA
		V _R = 600 V; T _j = 125 °C	-	-	200	μA
Dynamic cł	naracteristics	I				
Q _r recovered charge	recovered charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17	-	nC
		I _F = 8 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-	90	-	nC
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 7$	-	19	-	ns

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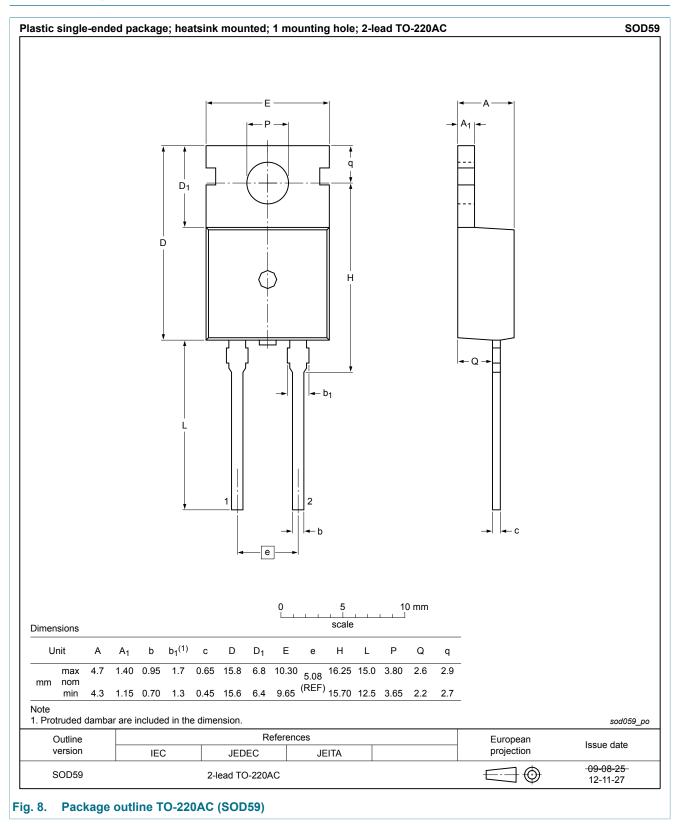
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{d} I_F/\text{d} t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	12	18	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	A
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	6	A



 $V_0 = 1.581 \text{ V}; \text{ R}_S = 0.043 \Omega$

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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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